Seminar #1

This section consists of 2 topics and both are required to be presented during the 1st seminar, week 4. Each group (3 or 4 people) should prepare for one presentation.

Topic 1

Select one power electronic equipment in your daily life and:

- Describe its function, input and output features
- Take a picture and then differentiate as well as mark down:
 - ♦ Power stage
 - ♦ Drive circuit
 - ◆ Control circuit
- Find the model of the power electronic device and component used in this equipment and describe its major parameters

(Such a power electronic equipment could be found in the Lab of Department of Industrial Automation, East-2 Building.)

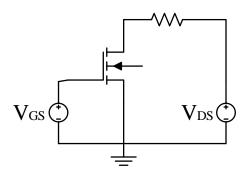
Topic 2

This topic aims to help you get a basic understanding of power electronic devices through simulation.

Each group will be assigned with a typical fully-controllable power device (MOSFET or IGBT) of certain model. The work to be done includes:

- 1. Carrying out simulation in LTspice to test the characteristics of the assigned device
- 2. Comparison between simulation results and the characteristics given by datasheet

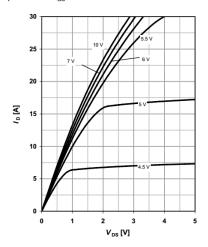
The testing circuit for **MOSFET** is shown as below.



The characteristics required to test includes:

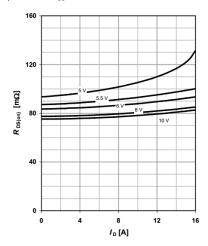
1. Output characteristics $(I_D = f(V_{DS}))$ under different V_{GS}

 $I_{\rm D}$ =f($V_{\rm DS}$); $T_{\rm j}$ =25 °C parameter: $V_{\rm GS}$



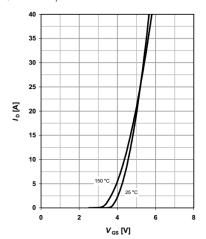
2. Drain-source on resistance $(R_{DS(on)} = f(I_D) \text{ under different } V_{GS})$

 $R_{\,\mathrm{DS(on)}}$ =f($I_{\,\mathrm{D}}$); $T_{\,\mathrm{j}}$ =25 °C parameter: $V_{\,\mathrm{GS}}$



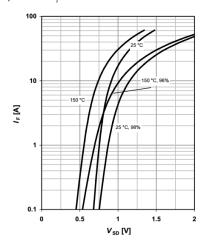
3. Transfer characteristics $(I_D = f(V_{GS}))$ with fixed V_{DS}

 $I_{\rm D} = f(V_{\rm GS}); |V_{\rm DS}| > 2|I_{\rm D}|R_{\rm DS(on)max}$ parameter: $T_{\rm i}$



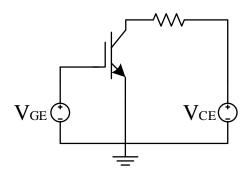
4. Forward characteristics of reverse diode $(I_F = f(V_{SD}))$

 $I_F = f(V_{SD})$ parameter: T_j



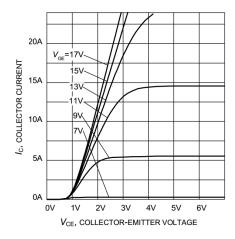
5. Switching waveform (real-time simulation, V_{GS} being pulsating signal)

The testing circuit for **IGBT** is shown as below.

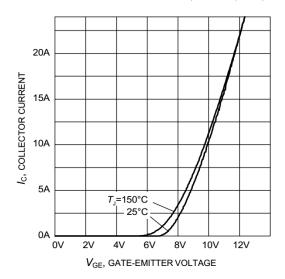


The characteristics required to test includes:

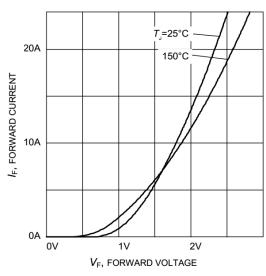
1. Output characteristics $(I_C = f(V_{CE}) \text{ under different } V_{GE})$



2. Transfer characteristics ($I_C = f(V_{GE})$ with fixed V_{CE})



3. Forward characteristics of reverse diode $(I_F = f(V_{EC}))$



4. Switching waveform (real-time simulation, V_{GE} being pulsating signal)

The installation file of LTspice as well as corresponding datasheet, tutorial and guide documents are available in **Curriculum Resource**.